

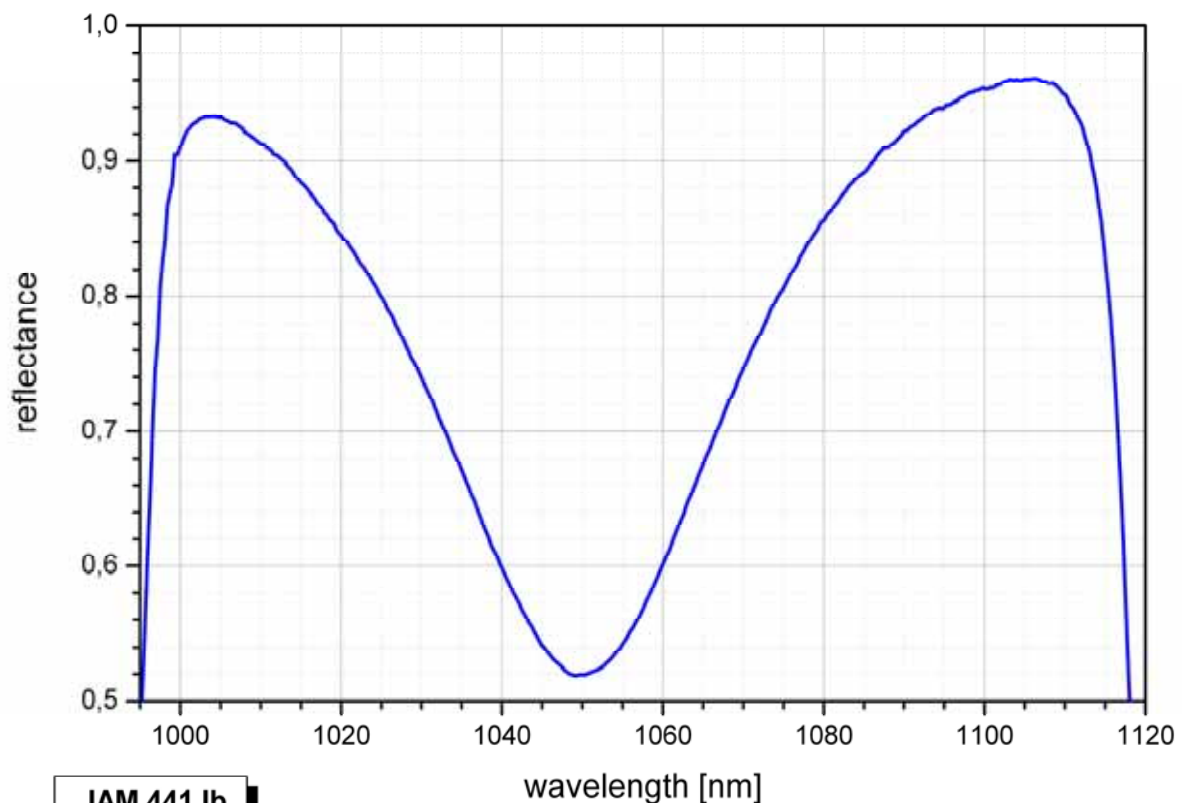
SAM™ Data Sheet SAM-1064-35-10ps-x, $\lambda = 1064 \text{ nm}$

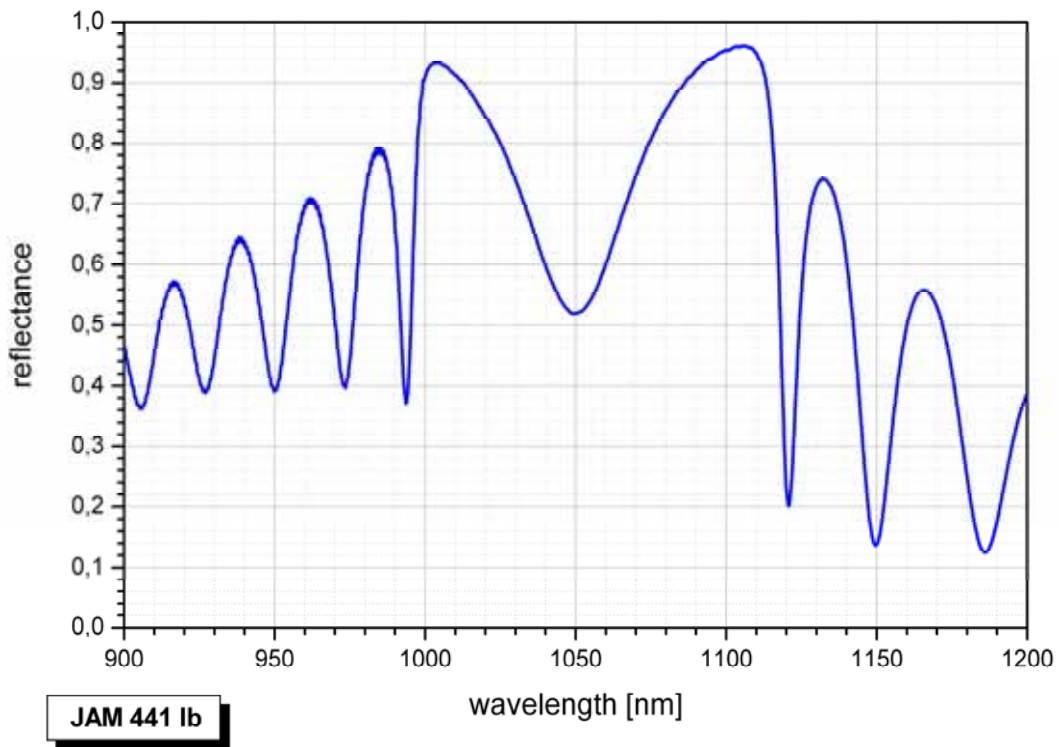
Laser wavelength	$\lambda = 1064 \text{ nm}$
High reflection band (R > 50%)	$\lambda = 1000 \dots 1100 \text{ nm}$
Absorbance	$A_0 = 35 \%$, resonant
Modulation depth	$\Delta R = 18 \%$
Non-saturable loss	$A_{ns} = 17 \%$
Saturation fluence	$\Phi_{sat} = 40 \mu\text{J}/\text{cm}^2$
Relaxation time constant	$\tau \sim 10 \text{ ps}$
Damage threshold	$\Phi = 1.5 \text{ mJ}/\text{cm}^2$
Chip area	4mm x 4mm; other dimensions on request
Chip thickness	450 μm
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm \varnothing
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm \varnothing
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm \varnothing
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm \varnothing
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance





Saturation measurement of a SAM-1064-25 from the same wafer

